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INIEC	RMATION D	NICCI	OSLIDE	Application Number	09/535,015	
				Filing Date	March 24, 2000	
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	(use as many sheets	as neces	ssary) .	Group Art Unit	2811	
				Examiner Name	S. Crane	
Sheet	neet 1 of 1			Attorney Docket Number	0756-2131	

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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	TEMENT BY			Filing Date	March 24, 2000
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				Examiner Name	S. Crane
Sheet	1	of	1	Attorney Docket Number	0756-2131

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STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named Inventor (use es many sheets es necessary) 2811 **Group Art Unit** S. Crane **Examiner Name** 0756-2131 **Attorney Docket Number** Sheet

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				Filing Date	March 24, 2000	
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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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INFOR	MATION DISCLOSURE STA	TENT	Applicants: Shupei YAN	AAZAKI et	al. T	<del></del>
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Filing Date	March 24, 2000
First Named Inventor	Shunpei YAMAZAKI et al.
Group Art Unit	2811
Examiner Name	S. Crane
Attorney Docket Number	0756-2131

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				Examiner Name	S. Crane
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INFORMATION DISCLOSURE				Application Number	09/535,015		
				Filing Date	March 24, 2000		
SIAI	STATEMENT BY APPLICANT		First Named Inventor	Shunpei YAMAZAKI et al.			
	(use as many sheets a	is necesso	(נימו	Group Art Unit	2811		
				Examiner Name	S. Crane		
Sheet	1	of	1	Attorney Docket Number	0756-2131		

				U.S. PATENT DOCUMEN	rs	
Examiner Initials*	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Releva Passages or Relevant Figures Appea
		Number	Kind Code <sup>2</sup> (If known)	Document	MM-DD-YYYY	
Sec		5,591,988		Arai et al.	01/07/1997	
346	-	5,953,597		Kusumoto et al.	09/14/1999	
<u> </u>		6,011,275		Ohtani et al.	01/04/2000	
SWC		6,331,718		Yamazaki et al.	12/18/2001	
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SW C	1	JР	06-314785		Suzawa et al.	11/8/1994		Abstract
SWC		JР	06-314787		Suzawa et al.	11/8/1994		Abstract
			ОТН	ER PRIOR	 ART – NON PATENT LITE	RATURE DOCUMENTS		1
Examiner Initials	Cite No.				or (in CAPITAL LETTERS), urnal, serial, symposium, catal publisher, city and/or coun	og, etc.)., date, page(s), volur		T²
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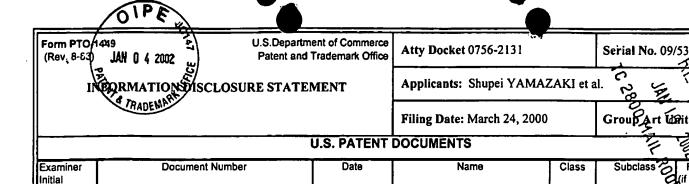
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<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Filing Date

(if appropriate)



03/17/1998

Suzawa et al.

5,728,259

Examiner CRANE Date Considered 10/18/02

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Form PTO-1 (Rev. 8-83)	449	Department of Commerce tentand reademark Office	Atty Docket 0756-		Serial No. 09	0/535,015
IN	FORMATION DISCLOSUI	₩ <b>.</b>	Applicants: Shupei YAMA	ZAKI et a	ıl.	
	P.	SEP 0 5 2001 S. PATENT I	Filing Date: March 24, 200	0	Group Art U	Jnit: 2825
		PADENA S. PATENT	DOCUMENTS			
Examiner Initial	Document Number	Date	Name	Class	Subdass	Filing Date (if appropriate)
SWC.	3,890,632	06/17/1975	Ham et al.	1		
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Initial						Yes No
SW(	07-335900	12/22/1995	JP			Eng Abst
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Examiner Initial						
521	Baker, Jr. et al., "Field Effe	ect Transistor", pp. 849, 19	968, IBM Technical Disclos	ure Bullet	in, Vol. 11, No	o. 7
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INFO	RMATION DISCLOSURE STA	TEMENT	Applicant: Shunpei YAM	MAZAKI et al.		S015				
•	(Use several sheets if necessary)		Filing Date: March 24,	2000	Group: 2811	/535 /24/				
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SW7	5,403,772	04/04/95	Zhang et al							
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Suc	R.J. Nemanich et al, "Initial Pl Symp. Proc., Vol. 25, 1984	hase Formation a	at the Interface of Ni,	Pd, or Pt a	and Si", Mat. f	Res. Soc.				
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Form PTC-1449 (Rev. 8-83)

U.S. Department of Commerce Patent and Trademark Office Attorney Docket No. 0756-2131

Serial No. Not Yet Assigned

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(Use several sheets if necessary)

Filing Date: March 24, 2000

Applicant: Shunpei YAMAZAKI et al.

Group: 2811

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) W	5,595,923	01/21/97	Zhang et al			
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Applicant: Shunpei YAMAZAKI et al.

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Group 2811

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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